

## AOS Semiconductor Product Reliability Report



**Plastic Encapsulated Device** 

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This AOS product reliability report summarizes the qualification result for AOTF2606L. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AOTF2606L passes AOS quality and reliability requirements. The released product will be categorized by the process family and be routine monitored for continuously improving the product quality.

Test Item	Test Condition	Time Point	Total Sample Size	Number of Failures	Reference Standard
HTGB	Temp = 150°C , Vgs=100% of Vgsmax	168 / 500 / 1000 hours	924 pcs	0	JESD22-A108
HTRB	Temp = 150°C, Vds=80% of Vdsmax	168 / 500 / 1000 hours	924 pcs	0	JESD22-A108
HAST	130°C , 85%RH, 33.3 psia, Vds = 80% of Vdsmax	96 hours	693 pcs	0	JESD22-A110
H3TRB	85°C , 85%RH, Vds = 80% of Vdsmax	1000 hours	693 pcs	0	JESD22-A101
Autoclave	121°C , 29.7psia, RH=100%	96 hours	924 pcs	0	JESD22-A102
Temperature Cycle	-65°C to 150°C , air to air,	1000cycles	924 pcs	0	JESD22-A104
HTSL	Temp = 150°C	1000 hours	693 pcs	0	JESD22-A103
IOL	∆ Tj = 100°C	8572 cycles	693 pcs	0	AEC Q101
Resistance to Solder Heat	Temp = 270°C	15 seconds	30 pcs	0	JESD22-B106

## I. Reliability Stress Test Summary and Results

**Note:** The reliability data presents total of available generic data up to the published date.

## II. Reliability Evaluation

## FIT rate (per billion): 1.91 MTTF = 59839 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate =  $Chi^2 \times 10^9 / [2 (N) (H) (Af)] = 1.91$ MTTF =  $10^9 / FIT = 59839$  years

**Chi**<sup>2</sup> = Chi Squared Distribution, determined by the number of failures and confidence interval  $\mathbf{N}$  = Total Number of units from burn-in tests

H = Duration of burn-in testing

**Af** = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse =  $55^{\circ}C$ ) Acceleration Factor [**Af**] = **Exp** [Ea / k (1/Tj u - 1/Tj s)]

Acceleration	Factor	ratio	list:	
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	deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af 2	259	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u =The use junction temperature in degree (Kelvin), K = C+273.16

 $\mathbf{k}$  = Boltzmann's constant, 8.617164 X 10<sup>-5</sup>eV / K